

FAST - [resistor.wsp.1]

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Drafts

Pending

Active

L1: (44) ("4,336,603") or ("4,380,057") or (

L2: (116050) ((non adj volatile) or flash) an

L3: (37482) 2 and (row\$1 or column\$1)

L4: (9220) 3 and ((source adj drain) or sourc

L5: (988) 4 and (dielectric).clm.

L6: (880) 5 and (conduct\$3 or wordline\$1)

L7: (594) 6 and (direction or orthogonal)

L8: (334) 7 and (plurality near7 (cells or ro

L9: (306) 8 and gate\$1.clm.

L10: (296) 9 and (memory or cell\$1).clm.

Failed

Saved

(0) ("(thinadjfilm)nearresistor").PN.

(0) ("(thinadjfilm)nearresistor").PN.

(150130) thin adj film

(14857) (thin adj film) and resistor

(2054) ((thin adj film) and resistor) and ((t

(1735) (((thin adj film) and resistor) and ((

(801) (((thin adj film) and resistor) and ((

USPAT 4,336,603

USPAT 4,380,057

USPAT 4,380,057

USPAT 4,380,057

USPAT 4,380,057

USPAT 4,380,057

USPAT 4,380,057

USPAT 4,380,057

USPAT 4,380,057

USPAT 4,380,057

9 and (memory or cell\$1).clm.

Resistor

Resistor

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Resistor

| | U | I | PT | P | Document ID | Issue Dat | Pages | Title | Current OF | Current XR | Retrieval | Inventor | S | C | | | | |
|-----|---|---|----|---|-------------|-----------|-------|-------------------------|------------|------------|-----------|--------------------|---|---|---|---|---|---|
| 142 | F | F | F | F | US 6574131 | 20030603 | | Depletion mode | 365/145 | 257/295 | | Salling, Craig T. | F | F | F | F | F | F |
| | | | | | B1 | | | ferroelectric memory de | | 257/E21.66 | | | | | | | | |
| 144 | F | F | F | F | US 6570214 | 20030527 | | Scalable stack-gate | 257/315 | 257/314 | | Wu, Ching-Yuan | F | F | F | F | F | F |
| | | | | | B1 | | | flash memory cell and i | | 257/321 | | | | | | | | |
| 149 | F | F | F | F | US 6570211 | 20030527 | | 2Bit/cell architecture | 257/314 | 257/315 | | He, Yue-song et | F | F | F | F | F | F |
| | | | | | B1 | | | for floating gate flash | | 257/E21.67 | | al. | | | | | | |
| 150 | F | F | F | F | US 6544844 | 20030408 | | Method for forming a | 438/257 | 257/E21.20 | | Chang, Yun et al. | F | F | F | F | F | F |
| | | | | | B2 | | | flash memory cell havin | | 9 | | | | | | | | |
| 151 | F | F | F | F | US 6534816 | 20030318 | | Method and apparatus | 257/314 | 257/E21.68 | | Caywood, John | F | F | F | F | F | F |
| | | | | | B1 | | | for injecting charge on | | 2 | | | | | | | | |
| 152 | F | F | F | F | US 6532170 | 20030311 | | Nonvolatile | 365/185.1 | 365/185.05 | | Madurawe, Raminda | F | F | F | F | F | F |
| | | | | | B1 | | | configuration cells and | | 1 | | U. et al. | | | | | | |
| 153 | F | F | F | F | US 6521495 | 20030218 | | Method of fabricating a | 438/257 | 257/E21.68 | | Shone, Moon et al. | F | F | F | F | F | F |
| | | | | | B2 | | | non-volatile memory dev | | 2 | | | | | | | | |
| 154 | F | F | F | F | US 6518618 | 20030211 | | Integrated memory cell | 257/315 | 257/333 | | Fazio, Albert et | F | F | F | F | F | F |
| | | | | | B1 | | | and method of fabricati | | 257/336 | | al. | | | | | | |
| 155 | F | F | F | F | US 6515889 | 20030204 | | Junction-isolated | 365/145 | 365/149 | | Salling, Craig T. | F | F | F | F | F | F |
| | | | | | B1 | | | deletion mode ferroele | | 365/185.01 | | et al. | | | | | | |
| 156 | F | F | F | F | US 6512263 | 20030128 | | Non-volatile memory | 257/316 | 257/315 | | Yuan, Jack H. et | F | F | F | F | F | F |
| | | | | | B1 | | | cell array having disco | | 257/326 | | al. | | | | | | |
| 157 | F | F | F | F | US 6509222 | 20030121 | | Process for | 438/201 | 257/314 | | Grossi, Alessandro | F | F | F | F | F | F |
| | | | | | B1 | | | manufacturing electroni | | 257/326 | | et al. | | | | | | |
| 158 | F | F | F | F | US 6500710 | 20021231 | | Method of manufacturing | 438/257 | 438/151 | | Nakagawa, Shinichi | F | F | F | F | F | F |

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